



1. Description

SS023N06NS, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for DC-DC and high speed switching applications.

KEY CHARACTERISTICS

Parameter	Value	Unit
V_{DS}	60	V
I_D	80	A
$R_{DS(on).typ}$	2.0	mΩ

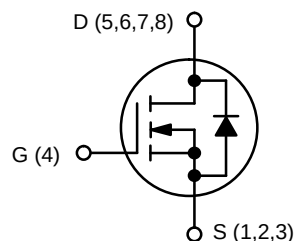
FEATURES

- Fast Switching
- Low On-Resistance ($R_{DS(on)} \leq 2.3m\Omega$)
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

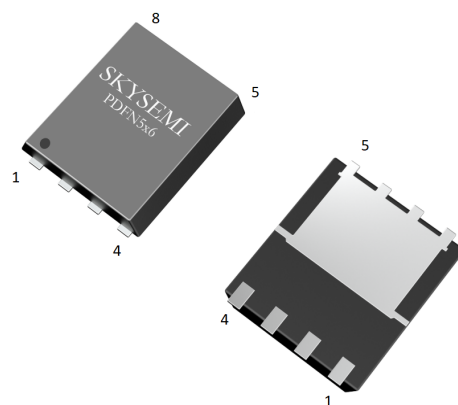
APPLICATIONS

- Switching applications
- DC-DC Converters
- BMS

Schematic Diagram



PDFN5×6



ORDERING INFORMATION

Ordering Code	Package	Product Code	Packing	Quantity
SS023N06NS	PDFN5×6	SS023N06NS	Reel	5000